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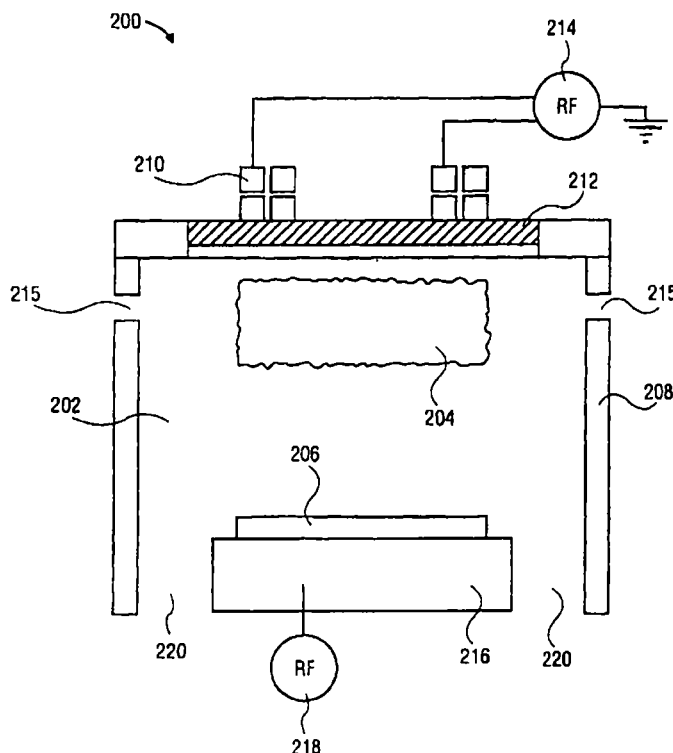
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(54) Title: METHOD AND APPARATUS FOR PRODUCING UNIFORM PROCESS RATES



(57) Abstract: A plasma processing apparatus for processing a substrate with a plasma is disclosed. The apparatus includes a first RF power source having a first RF frequency, and a process chamber. Further, the apparatus includes a substantially circular antenna operatively coupled to the first RF power source and disposed above a plane defined by the substrate when the substrate is disposed within the process chamber for processing. The substantially circular antenna being configured to induce an electric field inside the process chamber with a first RF energy generated by the first RF power source. The substantially circular antenna including at least a first pair of concentric loops in a first plane and a second pair of concentric loops in a second plane. The first pair of concentric loops and the second pair of concentric loops being substantially identical and symmetrically aligned with one another. The substantially circular antenna forming an azimuthally symmetric plasma inside the process chamber. The apparatus also includes a coupling window disposed between the antenna and the process chamber. The coupling window being configured to allow the passage of the first RF energy from the antenna to the interior of the process chamber. The coupling window having a first layer and a second layer. The second layer being configured to substantially suppress the

capacitive coupling formed between the substantially circular antenna and the plasma. The substantially circular antenna and the coupling window working together to produce a substantially uniform process rate across the surface of the substrate.

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